

NTE5511 thru NTE5513 Silicon Controlled Rectifier (SCR) 5 Amp

Description:

The NTE5511 thru NTE5513 all-diffused, three junction, silicon controlled rectifiers (SCR's) are intended for use in power-control and power-switching applications. These devices are available in a TO66 type package and have a blocking voltage capability of up to 600V and a forward current rating of 5A (rms value) at a case temperature of +75°C.

Features:

- Designed Especially for High-Volume Systems
- Readily Adaptable for PC Boards and Metal Heat Sinks
- Low Switching Losses
- High di/dt and dv/dt Capabilities
- Shorted Emitter Gate-Cathode Construction
- Forward and Reverse Gate Dissipation Ratings
- All-Diffused Construction Assures Exceptional Uniformity and Stability of Characteristics
- Direct-Soldered Internal Construction Assures Exceptional Resistance to Fatigue
- Symmetrical Gate-Cathode Construction Provides Uniform Current Density, Rapid Electrical Conduction, and Efficient Heat Dissipation
- All-Welded Construction and Hermetic Sealing
- Low Leakage Currents, Forward and Reverse
- Low Forward Voltage Drop at High Current Levels
- Low Thermal Resistance

Absolute Maximum Ratings: (For Operation with Sinusoidal AC Supply Voltage at a Frequency between 50Hz and 400Hz, and with Resistive or Inductive Load)

Transient Peak Reverse Voltage (Non-Repetitive), V_{RM} (non-rep)	
NTE5511	330V
NTE5512	660V
NTE5513	700V
Peak Reverse Voltage (Repetitive), V_{RM} (rep)	
NTE5511	200V
NTE5512	400V
NTE5513	600V
Peak Forward Blocking Voltage (Repetitive), V_{FBOM} (rep)	
NTE5511	600V
NTE5512	600V
NTE5513	700V
Average DC Forward Current, $I_{F(av)}$ ($T_C = +75^\circ\text{C}$ mounted on heat sink, conduction angle or 180°)	
	3.2A
RMS Forward Current ($T_C = +75^\circ\text{C}$ mounted on heat sink), I_{FRMS}	
	5A
Peak Surge Current (For one cycle of applied voltage), $i_{FM(surge)}$	
	60A
Sub-Cycle Surge (Non-Repetitive, for a period of 1ms to 8.3ms), I^2t	
	15A ² sec
Rate of Change of Forward Current (Note 1), di/dt	
	200A/μs
Gate Power (Peak, Forward, or Reverse, for 10μs duration, Note 2), P_{GM}	
	13W
Average Gate Power (Note 2), P_{GAV}	
	500mW
Operating Case Temperature Range, T_C	
	-40° to +100°C
Storage Temperature Range, T_{stg}	
	-40° to +125°C

Note 1. $V_{FB} = V_{BOO}$ (min value), $I_{GT} = 200\text{mA}$, $0.5\mu\text{s}$ rise time

Note 2. Any values of peak gate current or peak gate voltage to give the maximum gate power is permissible.

Electrical Characteristics: (At Maximum Ratings, $T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Forward Breakover Voltage NTE5511	V _{BOO}	T _C = +100°C		200	—	—	V
NTE5512				400	—	—	V
NTE5513				600	—	—	V
Peak Blocking Forward Current NTE5511	I _{FBOM}	V _{FBO} = 200V	T _C = +100°C	—	0.10	1.5	mA
NTE5512		V _{FBO} = 400V		—	0.20	3.0	mA
NTE5513		V _{FBO} = 600V		—	0.40	4.0	mA
Peak Blocking Reverse Current NTE5511	I _{RBOM}	V _{RBO} = 200V	T _C = +100°C	—	0.05	0.75	mA
NTE5512		V _{RBO} = 400V		—	0.10	1.5	mA
NTE5513		V _{RBO} = 600V		—	0.20	2.0	mA
Forward Voltage Drop	V _F	I _F = 30A		—	2.15	2.80	V
DC Gate–Trigger Current	I _{GT}			—	8	15	mA
DC Gate–Trigger Voltage	V _{GT}			—	1.2	2.0	V
Holding Current	I _{Hold}			—	10	20	mA
Critical Rate of Applied Forward Voltage	dv/dt	V _{FB} = v _{BOO} (min), exponential rise, T _C = +100°C		10	200	—	V/μs
Turn–On Time (Delay Time + Rise Time)	t _{on}	V _{FB} = v _{BOO} (min), i _F = 4.5A, I _{GT} = 200mA, 0.1μs rise time		0.75	1.5	—	μs
Turn–Off Time (Reverse Recovery Time + Gate Recovery Time)	t _{off}	i _F = 2A, 50μs pulse width, dv _{FB} /dt = 20V/μs, di _r /dt = 30A/μs, I _{GT} = 200mA, T _C = +75°C		—	15	50	μs
Thermal Resistance, Junction–to–Case	R _{θJC}			—	—	4	°C/W

